

### **Amendments to the Claims**

This listing of claims will replace all prior versions, and listings, of claims in the application:

#### **Listing of Claims**

1-21. (Cancelled).

22. A nonvolatile memory on a semiconductor substrate, comprising:

- (a) a prepared semiconductor substrate;
- (b) a plurality of bit lines;
- (c) a plurality of trapping layer block structures; and
- (d) a plurality of word lines over corresponding members of the plurality of trapping

layer block structures, wherein widths of the trapping layer block structures are greater than widths of the word lines.

23. The nonvolatile memory of claim 22, and further comprising at least one dielectric disposed between the plurality of word lines and trapping layer block structures.

24. The nonvolatile memory of claim 22, wherein the plurality of trapping layer block structures comprises in sequence, a first oxide layer, a nitride layer, and a second oxide layer.

25. The nonvolatile memory of claim 22, wherein the plurality of trapping layer block structures overlaps portions of adjoining members of the plurality of bit lines.